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Low Voltage Single Supply SPDT Analog Switch

The NLAST4599 is an advanced high speed CMOS single pole – double throw analog switch fabricated with silicon gate CMOS technology. It achieves high speed propagation delays and low ON resistances while maintaining low power dissipation. This switch controls analog and digital voltages that may vary across the full power–supply range (from V_{CC} to GND).

The device has been designed so the ON resistance $(R_{\rm ON})$ is much lower and more linear over input voltage than $R_{\rm ON}$ of typical CMOS analog switches.

The channel select input structure provides protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. This input structure helps prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- Select Pin Compatible with TTL Levels
- Channel Select Input Over–Voltage Tolerant to 5.5 V
- Fast Switching and Propagation Speeds
- Break–Before–Make Circuitry
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^{\circ}C$
- Diode Protection Provided on Channel Select Input
- Improved Linearity and Lower ON Resistance over Input Voltage
- Latch-up Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; MM > 200 V
- Chip Complexity: 38 FETs
- NLVAST Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

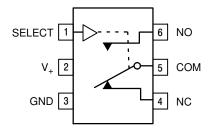
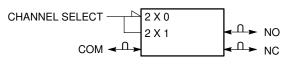
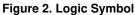
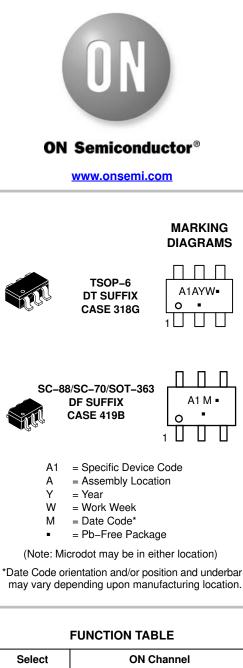


Figure 1. Pin Assignment







ON Channel					
NC					
NO					

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS (Note 1)

	Parameter	Symbol	Value	Unit
Positive DC Supply Volta	age	V _{CC}	-0.5 to +7.0	V
Analog Input Voltage (V	_{IO} or V _{COM})	V _{IS}	$-0.5 \le V_{IS} \le V_{CC} + 0.5$	V
Digital Select Input Volta	ge	V _{IN}	$-0.5 \leq V_l \leq +\ 7.0$	V
DC Current, Into or Out	of Any Pin	I _{IK}	±50	mA
Power Dissipation in Stil	Air SC-88 TSOP6	P _D	200 200	mW
Storage Temperature Ra	nge	T _{STG}	-65 to +150	°C
Lead Temperature, 1mm	from Case for 10 seconds	TL	260	°C
Junction Temperature U	nder Bias	TJ	150	°C
ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	V _{ESD}	2000 200 N/A	V
Latchup Performance	Above V_{CC} and Below GND at 125°C (Note 5)	ILATCHUP	±300	mA
Thermal Resistance	SC–88 TSOP6	θ_{JA}	333 333	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.
- 2. Tested to EIA/JESD22-A114-A
- 3. Tested to EIA/JESD22-A115-A
- 4. Tested to JESD22-C101-A
- 5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	V _{CC}	2.0	5.5	V
Digital Select Input Voltage	V _{IN}	GND	5.5	V
Analog Input Voltage (NC, NO, COM)	V _{IS}	GND	V _{CC}	V
Operating Temperature Range	T _A	-55	+125	°C
Input Rise or Fall Time $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V} \\ V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	t _r , t _f	0 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

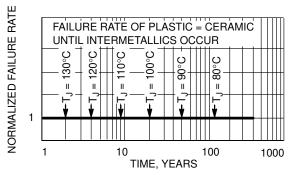


Figure 3. Failure Rate vs. Time Junction Temperature

DC CHARACTERISTICS – Digital Section (Voltages Referenced to GND)

				Guaranteed Limit			
Parameter	Condition	Symbol	V _{CC}	–55 to 25°C	<85°C	<125°C	Unit
Minimum High–Level Input Voltage, Select Input		V _{IH}	3.0 4.5 5.5	2.0 2.0 2.0	2.0 2.0 2.0	2.0 2.0 2.0	V
Maximum Low-Level Input Voltage, Select Input		V _{IL}	3.0 4.5 5.5	0.5 0.8 0.8	0.5 0.8 0.8	0.5 0.8 0.8	V
Maximum Input Leakage Current, Select Input	V _{IN} = 5.5 V or GND	I _{IN}	5.5	<u>+</u> 0.1	<u>+</u> 1.0	<u>+</u> 1.0	μΑ
Power Off Leakage Current	V _{IN} = 5.5 V or GND	I _{OFF}	0	<u>+</u> 10	<u>+</u> 10	<u>+</u> 10	μA
Maximum Quiescent Supply Current	Select and $V_{IS} = V_{CC}$ or GND	Icc	5.5	1.0	1.0	2.0	μΑ

DC ELECTRICAL CHARACTERISTICS – Analog Section

				Guara	nteed Lim	it	
Parameter	Condition	Symbol	v _{cc}	–55 to 25°C	<85°C	<125°C	Unit
Maximum "ON" Resistance (Figures 17 – 23)	$ \begin{array}{l} V_{IN} = V_{IL} \mbox{ or } V_{IH} \\ V_{IS} = GND \mbox{ to } V_{CC} \\ I_{IN}I \leq 10.0 \mbox{ mA} \end{array} $	R _{ON}	2.5 3.0 4.5 5.5	85 45 30 25	95 50 35 30	105 55 40 35	Ω
ON Resistance Flatness (Figures 17 – 23)	$ \begin{array}{l} V_{IN} = V_{IL} \text{ or } V_{IH} \\ I_{IN}I \leq 10.0 \text{ mA} \\ V_{IS} = 1V, 2V, 3.5V \end{array} $	R _{FLAT} (ON)	4.5	4	4	5	Ω
ON Resistance Match Between Channels		ΔR _{ON} (ON)	4.5	2	2	3	Ω
NO or NC Off Leakage Current (Figure 9)		I _{NC(OFF)} I _{NO(OFF)}	5.5	1	10	100	nA
COM ON Leakage Current (Figure 9)		I _{COM(ON)}	5.5	1	10	100	nA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

					G	uarant	teed M	ax Lin	nit			
			v_{cc}	VIS	-5	5 to 25	5°C	<8	5°C	<12	25°C	
Parameter	Test Conditions	Symbol	(V)	(V)	Min	Тур*	Max	Min	Max	Min	Max	Unit
Turn–On Time	$R_L = 300 \Omega, C_L = 35 pF$	t _{ON}	2.5	2.0	5	23	28	5	30	5	30	ns
(Figures 12 and 13)	(Figures 5 and 6)		3.0	2.0	5	16	21	5	25	5	25	
			4.5	3.0	2	11	16	2	20	2	20	
			5.5	3.0	2	9	14	2	20	2	20	
Turn–Off Time	$R_L = 300 \Omega, C_L = 35 pF$	t _{OFF}	2.5	2.0	1	7	12	1	15	1	15	ns
(Figures 12 and 13)	(Figures 5 and 6)		3.0	2.0	1	5	10	1	15	1	15	
			4.5	3.0	1	4	9	1	12	1	12	
			5.5	3.0	1	3	8	1	12	1	12	
Minimum Break-Before-	V _{IS} = 3.0 V (Figure 4)	t _{BBM}	2.5	2.0	1	12		1		1		ns
Make Time	$R_L = 300 \Omega$, $C_L = 35 pF$		3.0	2.0	1	11		1		1		
			4.5	3.0	1	6		1		1		
			5.5	3.0	1	5		1		1		
					Тур	oical @	25, VC	CC = 5	.0 V			
Maximum Input Capacitance, Select Input Analog I/O (switch off) Common I/O (switch off) Feedthrough (switch on)		C _{IN} C _{NO} or C _{NC} C _{COM} C _(ON)	8						pF			

*Typical Characteristics are at 25°C.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

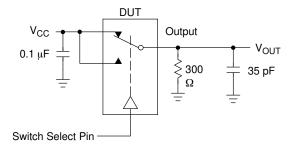
Parameter	Condition	Symbol	V _{CC} V	Typical 25°C	Unit
Maximum On–Channel –3dB Bandwidth or Minimum Frequency Response (Figure 10)	$V_{IN} = 0 \text{ dBm}$ V_{IN} centered between V_{CC} and GND (Figure 7)	BW	3.0 4.5 5.5	170 200 200	MHz
Maximum Feedthrough On Loss	$V_{IN} = 0 \text{ dBm} @ 100 \text{ kHz} \text{ to } 50 \text{ MHz}$ V_{IN} centered between V_{CC} and GND (Figure 7)	V _{ONL}	3.0 4.5 5.5	-2 -2 -2	dB
Off-Channel Isolation (Figure 10)	f = 100 kHz; V_{IS} = 1 V RMS V_{IN} centered between V_{CC} and GND (Figure 7)	V _{ISO}	3.0 4.5 5.5	-93 -93 -93	dB
Charge Injection Select Input to Common I/O (Figure 15)	$ \begin{array}{l} V_{IN} = V_{CC \ to} \ GND, \ F_{IS} = 20 \ \text{kHz} \\ t_r = t_f = 3 \ \text{ns} \\ R_{IS} = 0 \ \Omega, \ C_L = 1000 \ \text{pF} \\ Q = C_L \ ^* \ \Delta V_{OUT,} \ (\text{Figure 8}) \end{array} $	Q	3.0 5.5	1.5 3.0	рС
Total Harmonic Distortion THD + Noise (Figure 14)	F_{IS} = 20 Hz to 100 kHz, R_L = Rgen = 600 $\Omega,$ C_L = 50 pF V_{IS} = 5.0 V_{PP} sine wave	THD	5.5	0.1	%

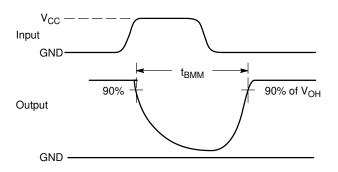
ORDERING INFORMATION

Device	Package	Shipping [†]
NLAST4599DFT2G	SC-88/SC-70/SOT-363 (Pb-Free)	3000 / Tape & Reel
NLAST4599DTT1G	TSOP-6	
NLVAST4599DTT1G*	(Pb–Free)	3000 / Tape & Reel

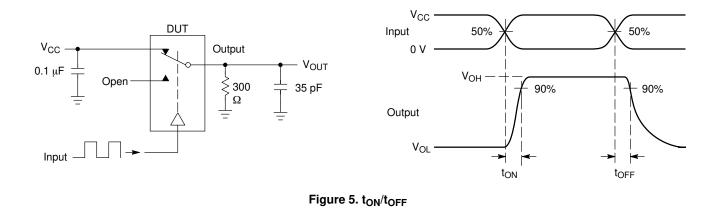
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *NLVAST Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and

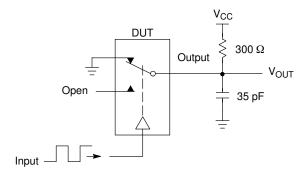
PPAP Capable.

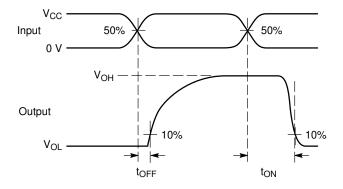


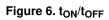


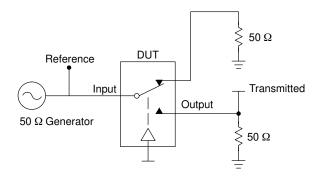










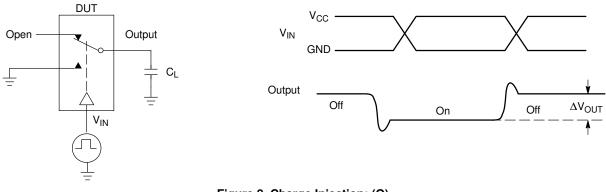


Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$\begin{split} V_{ISO} &= \text{Off Channel Isolation} = 20 \text{ Log } \left(\frac{V_{OUT}}{V_{IN}}\right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz} \\ V_{ONL} &= \text{On Channel Loss} = 20 \text{ Log } \left(\frac{V_{OUT}}{V_{IN}}\right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz} \text{ to } 50 \text{ MHz} \end{split}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

Figure 7. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}





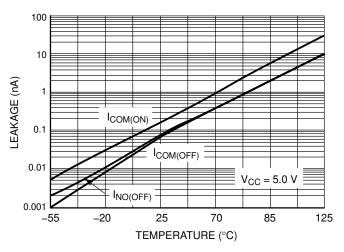
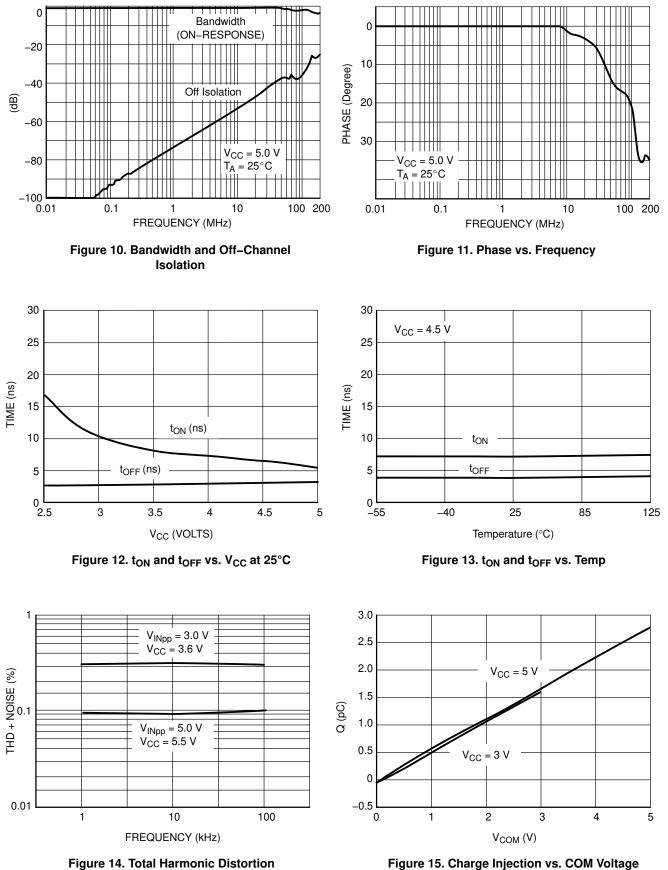
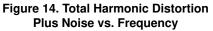
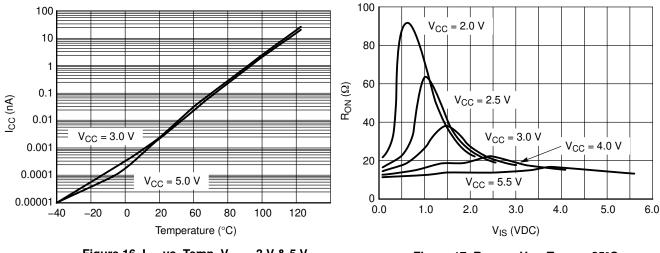


Figure 9. Switch Leakage vs. Temperature

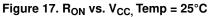


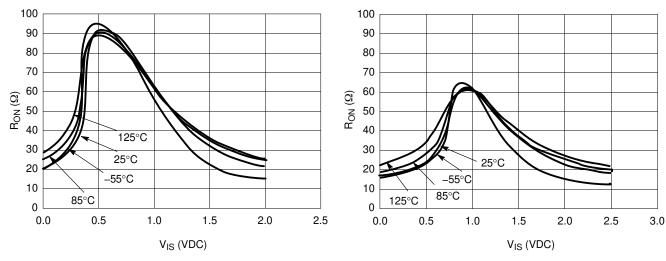


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25

20

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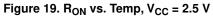
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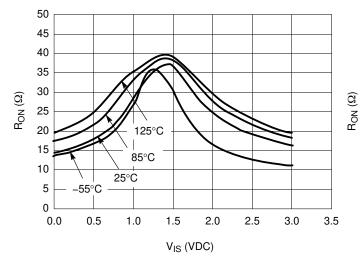
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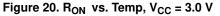
0

0.0











2.0 2.5

V_{IS} (VDC)

3.0 3.5

4.0

4.5

125°C

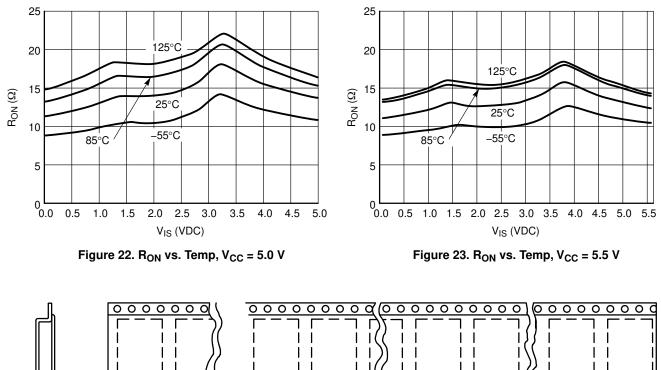
85°C

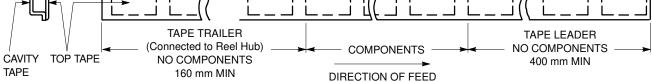
25°C

1.5

_55°C

0.5 1.0







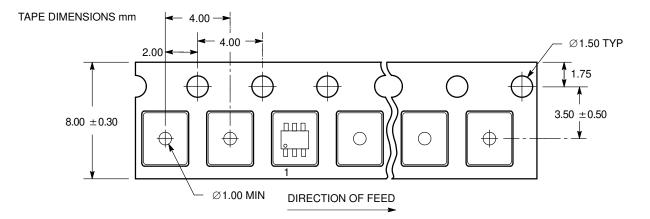
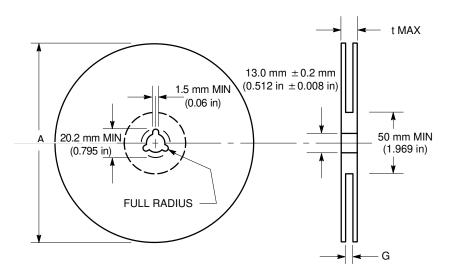


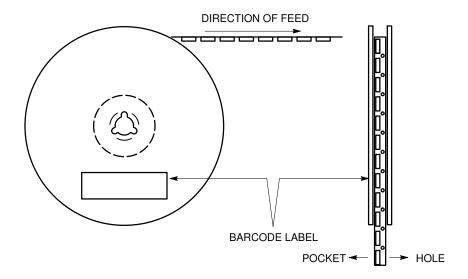
Figure 25. SC70-6/SC-88/SOT-363 DFT2 and SOT23-6/TSOP-6/SC59-6 DTT1 Reel Configuration/Orientation





REEL DIMENSIONS

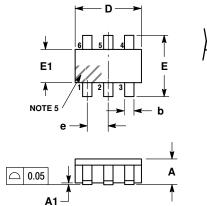
Tape Size	T and R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7 in)	8.4 mm, + 1.5 mm, –0.0 (0.33 in + 0.059 in, –0.00)	14.4 mm (0.56 in)

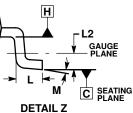


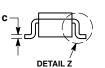


PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 **ISSUE V**







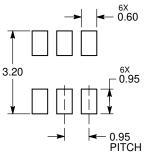
- NOTES:

 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.

 PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

	MILLIMETERS						
DIM	MIN	NOM	MAX				
Α	0.90	1.00	1.10				
A1	0.01	0.06	0.10				
b	0.25	0.38	0.50				
c	0.10	0.18	0.26				
D	2.90	3.00	3.10				
Е	2.50	2.75	3.00				
E1	1.30	1.50	1.70				
е	0.85	0.95	1.05				
L	0.20	0.40	0.60				
L2	0.25 BSC						
М	0°	-	10°				

RECOMMENDED SOLDERING FOOTPRINT*

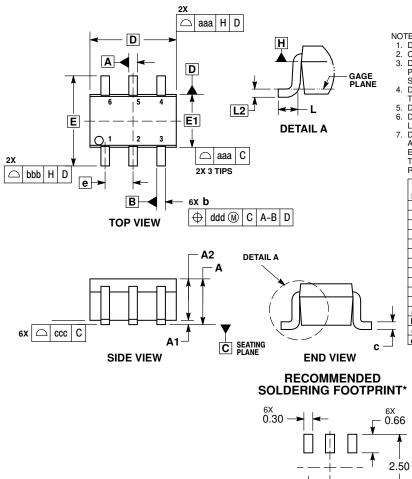


DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.

- CONTROLLING DIMENSION: MILLIMETERS. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRU-SIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS & AND ¢ APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION & AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MIL	LIMETE	RS		INCHES	5	
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α			1.10			0.043	
A1	0.00		0.10	0.000		0.004	
A2	0.70	0.90	1.00	0.027	0.035	0.039	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С	0.08	0.15	0.22	0.003	0.006	0.009	
D	1.80	2.00	2.20	0.070	0.078	0.086	
Ш	2.00	2.10	2.20	0.078	0.082	0.086	
E1	1.15	1.25	1.35	0.045	0.049	0.053	
е	0.65 BSC			0	.026 BS	С	
Г	0.26	0.36	0.46	0.010	0.014	0.018	
L2		0.15 BS	SC	0.006 BSC			
aaa		0.15			0.006		
bbb		0.30		0.012			
ccc		0.10		0.004			
ddd		0.10 0.004					

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and

DIMENSIONS: MILLIMETERS

Mounting Techniques Reference Manual, SOLDERRM/D.

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